

MANUFACTURING METHOD OF SINGLE-CRYSTAL SILICON SUBSTRATE

ABSTRACT

After separation layers are formed inside a single-crystal silicon ingot, a single-crystal silicon substrate is split off from the single-crystal silicon ingot with use of these separation layers as the point of origin. This can improve the productivity of the single-crystal silicon substrate compared with the case of manufacturing the single-crystal silicon substrate from the single-crystal silicon ingot by a wire saw.

[FIG. 3]